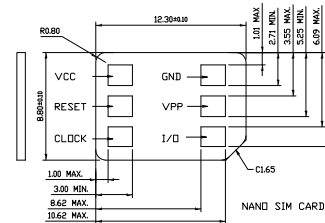
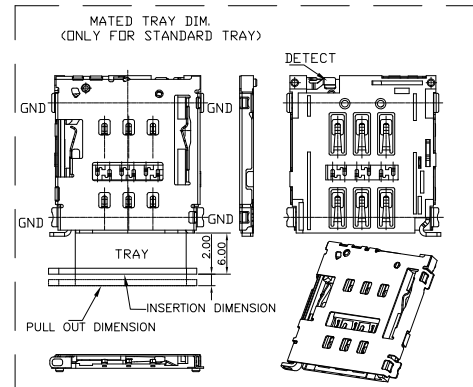
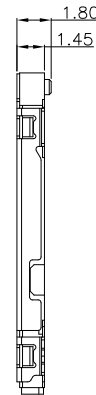
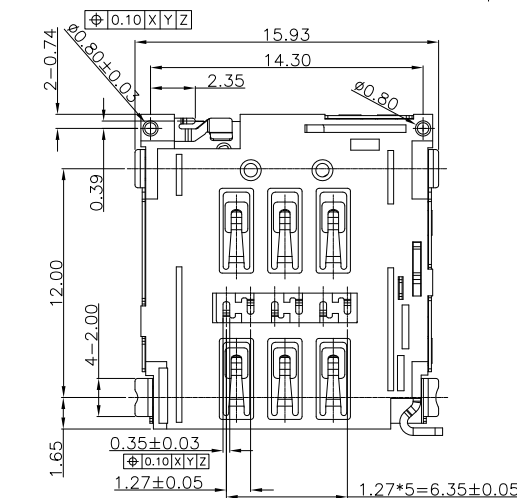
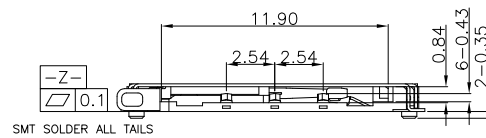
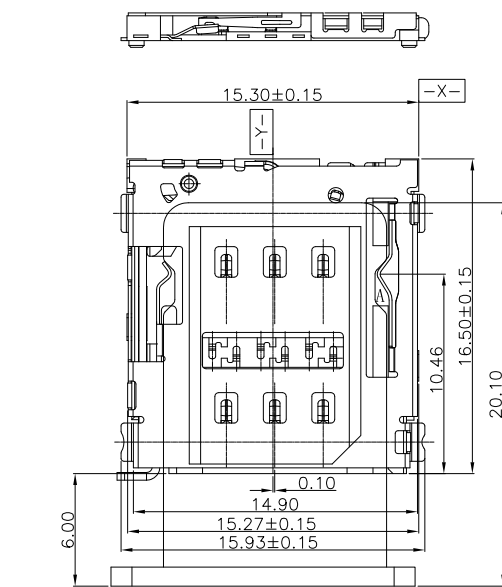
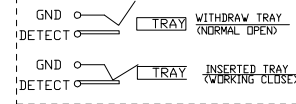


GP Component

REV.	ECN NO.	LOCATIONS	DESCRIPTION	DATE	DESIGN
AO			Initial	2017/06/13	Phebe Su

Circuit Diagram For Switch



NOTES:

- ELECTRICAL CHARACTERISTICS:
 - 1-1. CURRENT RATING: 1 Amp/PIN. MAX.
 - 1-2. VOLTAGE: 30V DC. MAX.
 - 1-3. LOW LEVEL CONTACT RESISTANCE: 30 mOhms MAX. INITIALLY.
 - 1-4. DIELECTRIC WITHSTANDING VOLTAGE: 500V AC MIN. FOR 1 MINUTE.
 - 1-5. INSULATION RESISTANCE: 100MOhms MIN. (DC 500V FOR 1 MINUTE)
- MECHANICAL CHARACTERISTICS:
 - 2-1. DURABILITY: 1000 CYCLES.
 - 2-2. OPERATING FORCE (INSERTING & WITHDRAWAL): 1N-10N.
- ENVIRONMENTAL CHARACTERISTICS:
 - 3-1. OPERATING TEMP. RANGE: -40°C TO 85°C. (INCLUDING TERMINAL TEMP. RISE)
 - 3-2. STORAGE TEMP.: -40°C TO 85°C.

MATRIX PART NO:

Matrix NANO SIM

MSM - 02 - 01 - 06 - 15 - 44

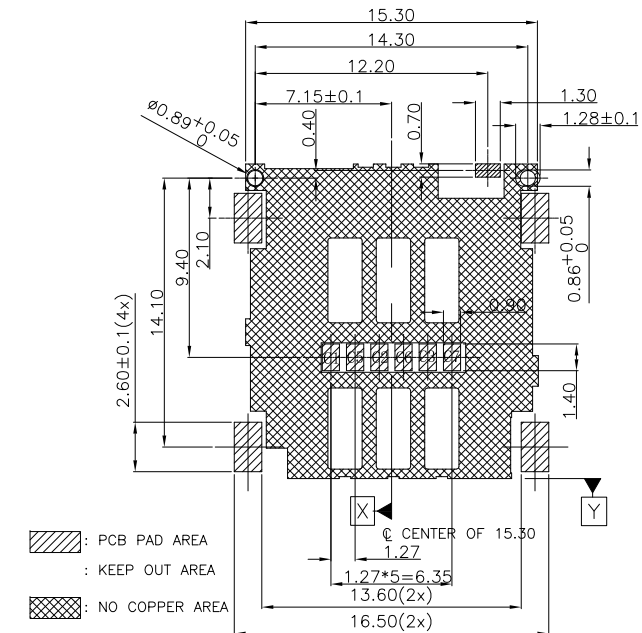
01: Push
02: Non-Push

Plating
01: G/F

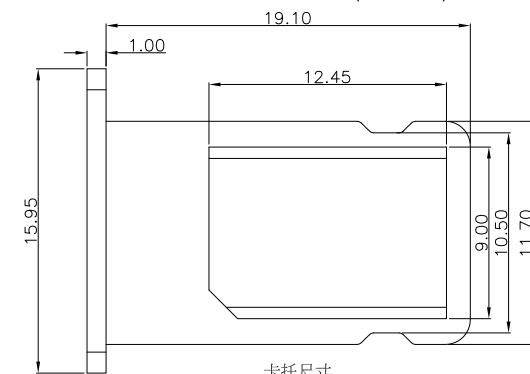
Series Number

Height

Pin number
06: 6pin



PCB PAD AREA
KEEP OUT AREA
NO COPPER AREA

RECOMMENDED PC BOARD LAYOUT
TOLERANCE: ±0.05(TOP VIEW)

卡托尺寸

NO	VARIETY	QTY	MATERIAL	REMARK
Matrix Electronics Co.,Ltd				
TOLERANCE:		DESIGN BY :	DATE :	PART NAME:
X. X		Phebe Su	2017/06/13	Nano SIM 带卡托
X. XX		CHECKED BY:	DATE :	PART NO.
X. XXX		Vicky Hsieh	2017/06/13	MSM-02-01-06-15-44
ANGLE:		APPROVED BY1:	DATE :	MOLD NO.
±3°		Richard Hsieh	2017/06/13	NA
UNIT: mm [inch]		APPROVED BY2:	DATE :	DRAW NO.
SCALE:1:1		Richard Hsieh	2017/06/13	SHEET NO.
SIZE:A4				1 OF 1